

Field Effect Transistor - N-Channel, Enhancement Mode

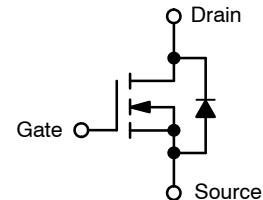
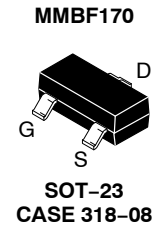
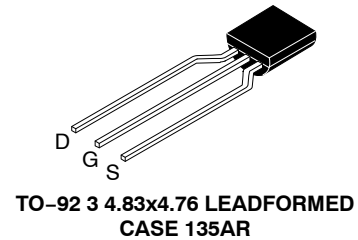
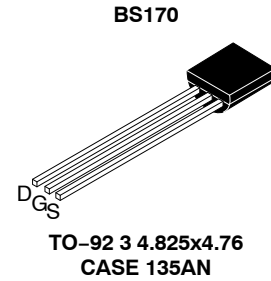
BS170, MMBF170

General Description

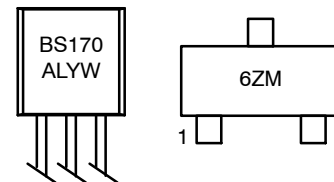
These N-Channel enhancement mode field effect transistors are produced using onsemi's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500 mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- High Density Cell Design for Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- High Saturation Current Capability
- These are Pb-Free Devices



MARKING DIAGRAM



BS170, 6Z = Device Code
 A = Assembly Plant Code
 L = Wafer Lot Number
 YW = Assembly Start Week
 M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter		BS170	MMBF170	Unit
V _{DSS}	Drain–Source Voltage		60		V
V _{DGR}	Drain–Gate Voltage (R _{GS} ≤ 1 MΩ)		60		V
V _{GSS}	Gate–Source Voltage		±20		V
I _D	Drain Current	– Continuous	500	500	mA
		– Pulsed	1200	800	
T _J , T _{STG}	Operating and Storage Temperature Range		– 55 to 150		°C
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds		300		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	BS170	MMBF170	Unit
P _D	Maximum Power Dissipation Derate above 25°C	830 6.6	300 2.4	mW mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	150	417	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = 100 μA	All	60	–	–	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 25 V, V _{GS} = 0 V	All	–	–	0.5	μA
I _{GSSF}	Gate – Body Leakage, Forward	V _{GS} = 15 V, V _{DS} = 0 V	All	–	–	10	nA

ON CHARACTERISTICS (Note 1)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 1 mA	All	0.8	2.1	3	V
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 10 V, I _D = 200 mA	All	–	1.2	5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 200 mA	BS170	–	320	–	mS
		V _{DS} ≥ 2 V _{DS(on)} , I _D = 200 mA	MMBF170	–	320	–	

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0 MHz	All	–	24	40	pF
C _{oss}	Output Capacitance		All	–	17	30	pF
C _{rss}	Reverse Transfer Capacitance		All	–	7	10	pF

SWITCHING CHARACTERISTICS (Note 1)

t _{on}	Turn–On Time	V _{DD} = 25 V, I _D = 200 mA, V _{GS} = 10 V, R _{GEN} = 25 Ω	BS170	–	–	10	ns
		V _{DD} = 25 V, I _D = 500 mA, V _{GS} = 10 V, R _{GEN} = 50 Ω	MMBF170	–	–	10	
t _{off}	Turn–Off Time	V _{DD} = 25 V, I _D = 200 mA, V _{GS} = 10 V, R _{GEN} = 25 Ω	BS170	–	–	10	ns
		V _{DD} = 25 V, I _D = 500 mA, V _{GS} = 10 V, R _{GEN} = 50 Ω	MMBF170	–	–	10	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

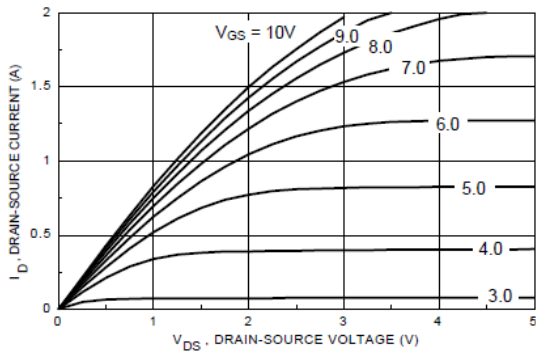


Figure 1. On-Region Characteristics

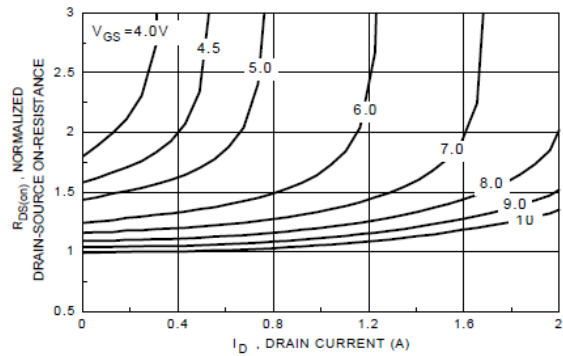


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

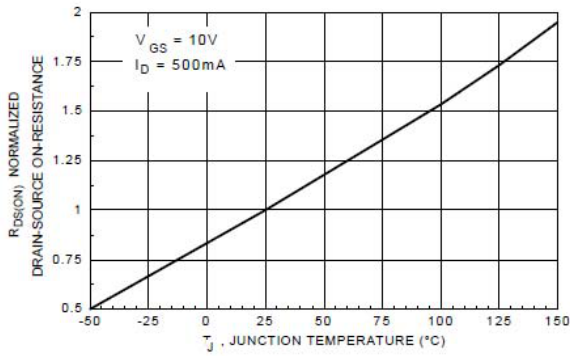


Figure 3. On-Resistance Variation with Temperature

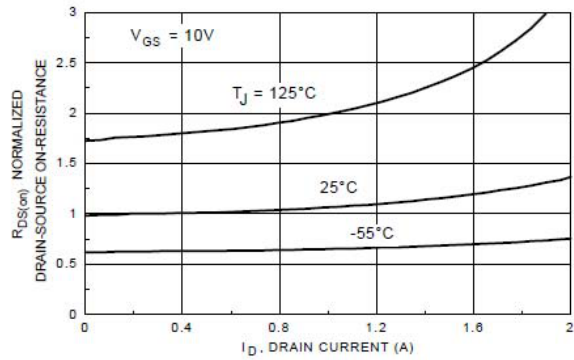


Figure 4. On-Resistance Variation with Drain Current and Temperature

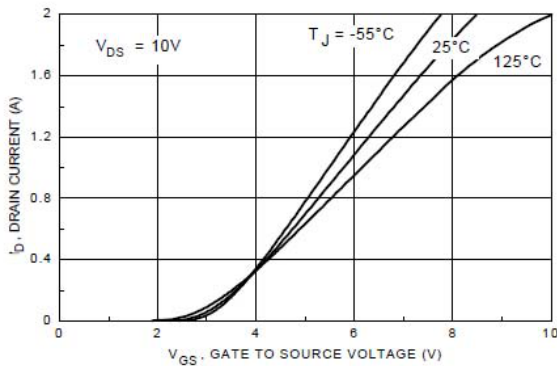


Figure 5. Transfer Characteristics

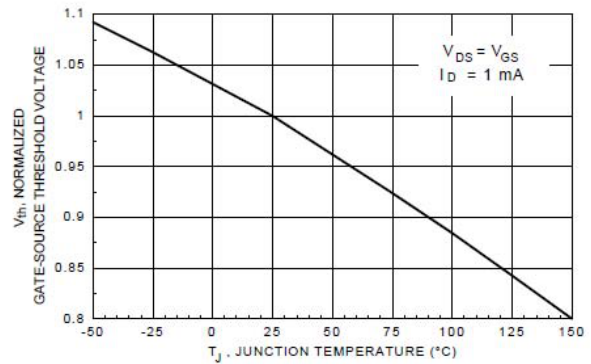


Figure 6. Gate Threshold Variation with Temperature

TYPICAL ELECTRICAL CHARACTERISTICS (continued)

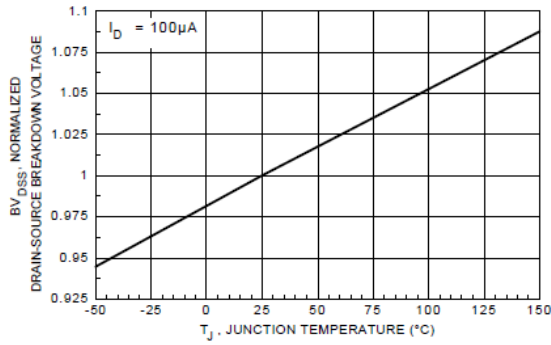


Figure 7. Breakdown Voltage Variation with Temperature

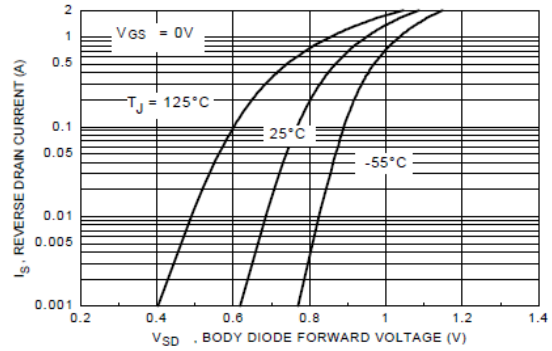


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature

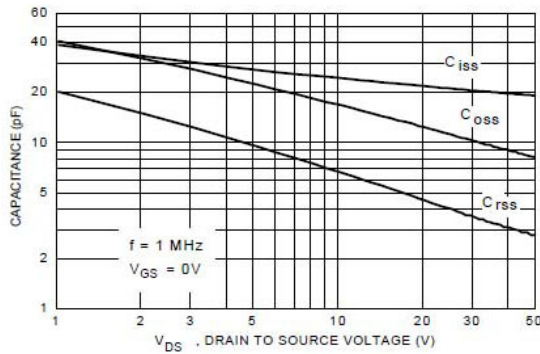


Figure 9. Capacitance Characteristics

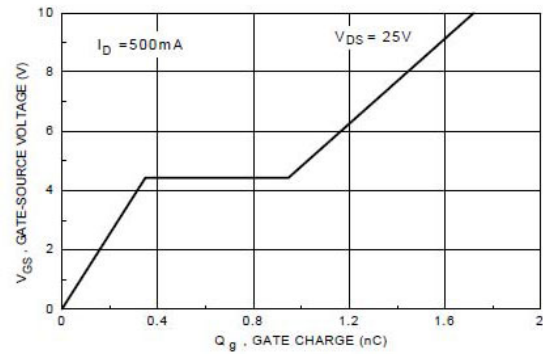


Figure 10. Gate Charge Characteristics

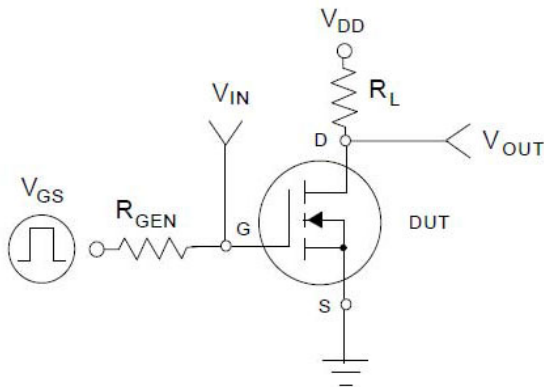


Figure 11. Switching Test Circuit

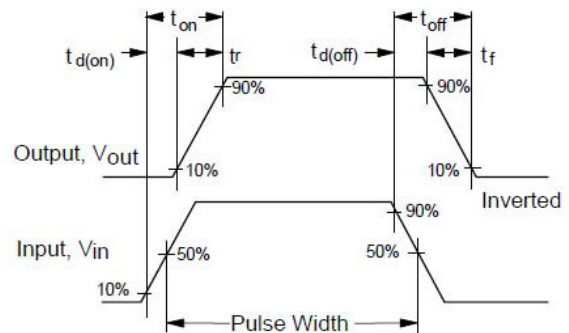


Figure 12. Switching Waveforms

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TYPICAL ELECTRICAL CHARACTERISTICS (continued)

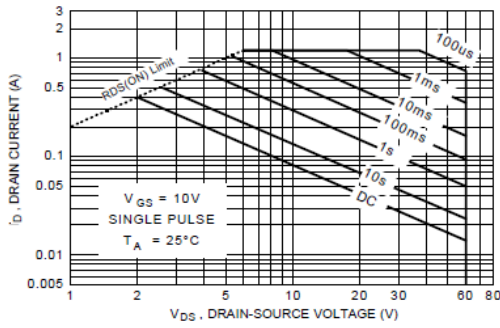


Figure 13. BS170 Maximum Safe Operating Area

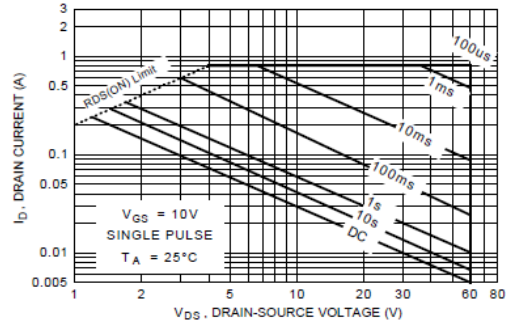


Figure 14. MMBF170 Maximum Safe Operating Area

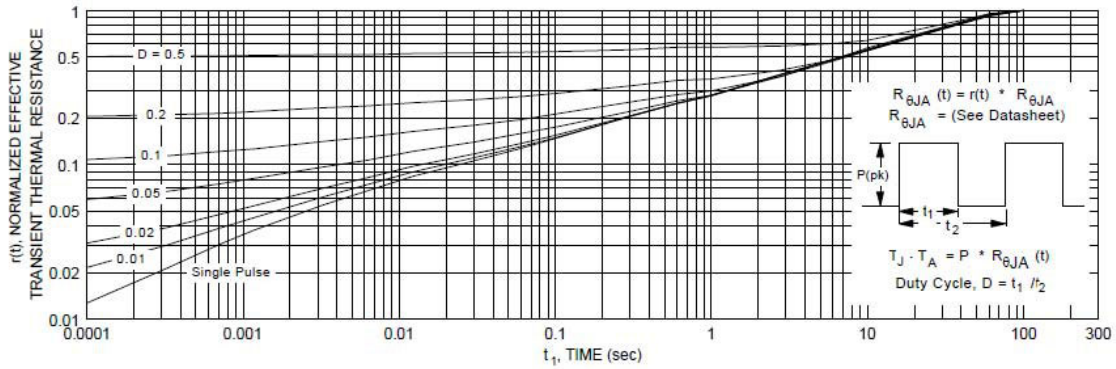


Figure 15. TO-92, BS170 Transient Thermal Response Curve

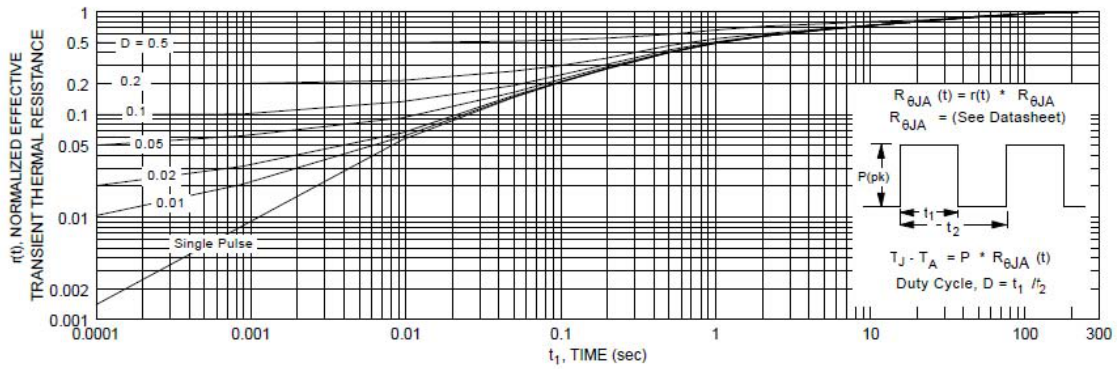


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve